Ordering number:EN4890

FX607

N-Channel Silicon MOSFET

Ultrahigh-Speed Switching, Motor Driver Applications

Features

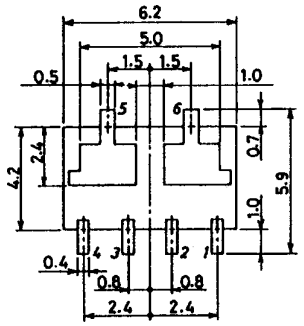
- Composite type composed of two low ON-resistance N-channel MOSFET chips for ultrahigh-speed switching and low-voltage drive.
- Facilitates high-density mounting.
- The FX607 is formed with two chips, each being equivalent to the 2SK2260, placed in one package.
- Matched pair characteristics.

Package Dimensions

unit:mm

2120

[FX607]

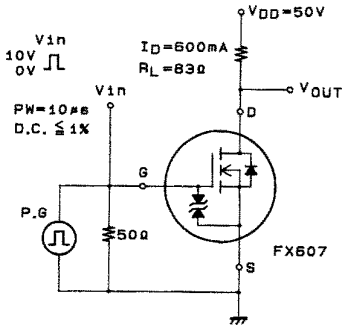


1:Gate1
2:Source1
3:Source2
4:Gate2
5:Drain2
6:Drain1

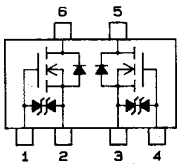
SANYO:XP6

(Bottom view)

Switching Time Test CIrcuit



Electrical Connection



1:Gate1
2:Source1
3:Source2
4:Gate2
5:Drain2
6:Drain1

(Top view)

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		150	V
Gate-to-Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		1.2	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	4.8	A
Allowable Power Dissipation	P_D	Tc=25˚C, 1 unit	6	W
	P_D	Mounted on ceramic board (750mm²×0.8mm) 1 unit	1.5	W
Total Dissipation	P_T	Mounted on ceramic board (750mm²×0.8mm)	2	W
Channel Temperature	Tch		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

- Marking:607

Continued on next page.

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Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
D-S Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	150			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=150V, V_{GS}=0			100	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±18V, V_{DS}=0			±10	μA
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=10V, ID=1mA	1.5		2.5	V
Forward Transfer Admittance	$\|Y_{fs}\|$	V_{DS}=10V, I_D=600mA	0.8	1.1		S
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	I_D=600mA, V_{GS}=10V		1.6	2.2	Ω
Input Capacitance	Ciss	V_{DS}=20V, f=1MHz		80		pF
Output Capacitance	Coss	V_{DS}=20V, f=1MHz		25		pF
Reverse Transfer Capacitance	Crss	V_{DS}=20V, f=1MHz		8.5		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		10		ns
Rise Time	t_r	See specified Test Circuit		15		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		50		ns
Fall Time	t_f	See specified Test Circuit		30		ns
Diode Forward Voltage	V_{SD}	I_S=1.2A, V_{GS}=0		1.0		V